

Docket No. 239515US2

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

IN RE APPLICATION OF: Keisuke YONEHAMA, et al.

SERIAL NO: NEW APPLICATION

GAU:

FILED: HEREWITH

EXAMINER:

FOR: A SEMICONDUCTOR MEMORY DEVICE HAVING A GATE ELECTRODE AND A DIFFUSION LAYER AND  
A MANUFACTURING METHOD THEREOF

**INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97**

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

**REFERENCES**

- The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- A check is attached in the amount required under 37 CFR §1.17(p).

**RELATED CASES**

- Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- A check is attached in the amount required under 37 CFR §1.17(p).

**CERTIFICATION**

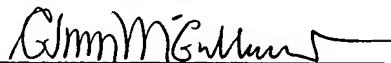
- Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

**DEPOSIT ACCOUNT**

- Please charge any additional fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

IN RE APPLICATION OF: Keisuke YONEHAMA, et al.

SERIAL NO.: New Application

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AND A DIFFUSION LAYER AND A MANUFACTURING METHOD THEREOF

**STATEMENT OF RELEVANCY**

**Reference AO through AS on Form PTO-1449:**

These references show a local interconnect.

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 239515US2		SERIAL NO. NEW APPLICATION	
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Keisuke YONEHAMA, et al.					
		FILING DATE HEREWITH			GROUP		
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	5,659,500	8/19/97	Freidoon MEHRAD			
	AB	6,451,642 B1	9/17/02	Freidoon MEHRAD, et al.			
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
	AD	10-326896	12/8/98	Japan (with English Abstract)	<input type="checkbox"/>	<input checked="" type="checkbox"/>	x
	AP	11-265947	9/28/99	Japan (with English Abstract)	<input type="checkbox"/>	<input checked="" type="checkbox"/>	x
	AQ	6-334156	12/2/94	Japan (with English Abstract)	<input type="checkbox"/>	<input checked="" type="checkbox"/>	x
	AR	2002-76147	3/15/02	Japan (with English Abstract)	<input type="checkbox"/>	<input checked="" type="checkbox"/>	x
	AS	7-74326	3/17/95	Japan (with English Abstract)	<input type="checkbox"/>	<input checked="" type="checkbox"/>	x
	AT	9-129854	5/16/97	Japan (Corresponds to US 5,659,500)	<input type="checkbox"/>	<input checked="" type="checkbox"/>	x
	AU	2001-68571	3/16/01	Japan (Corresponds to US 6,451,642 B1)	<input type="checkbox"/>	<input checked="" type="checkbox"/>	x
	AV				<input type="checkbox"/>	<input checked="" type="checkbox"/>	
<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
	AW	H. WATANABE, et al. "NOVEL $0.44\mu m^2$ Ti-SALICIDE STI CELL TECHNOLOGY FOR HIGH-DENSITY NOR FLASH MEMORIES AND HIGH PERFORMANCE EMBEDDED APPLICATION," IEDM 98-975.					
	AX						
	AY						
	AZ					<input type="checkbox"/> Additional References sheet(s) attached	
Examiner				Date Considered			

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.